

Operational Amplifier, 36 V, 3 MHz, 0.95 mV Input Offset Voltage, Rail-to-Rail

NCS20231, NCV20231

The NCS2023x series of op amps feature a wide supply range of 2.7 V to 36 V with an input offset voltage as low as ±0.95 mV max. These op amps are available in single, dual, and quad channel configurations. Automotive qualified options are available under the NCV prefix with an optional extended operating temperature range from -40 °C to 150 °C. All other versions are specified over the operating temperature range from -40 °C to 125 °C.

Features

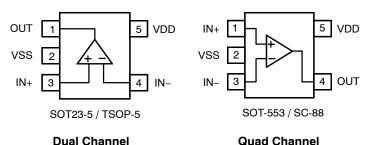
- Supply Voltage Range: 2.7 V to 36 V
- Temperature Range: -40 °C to 150 °C
- Unity Gain Bandwidth: 3 MHz
- Input Offset Voltage: ± 1.2 mV max, $T_A = -40$ to 150 °C
- Input Offset Voltage Drift: ±2 μV/°C max
- Common-Mode Input Voltage Range
 - Optimal: $V_{SS} 0.1$ to $V_{DD} 2 V$
 - Functional: $V_{SS} 0.1$ to $V_{DD} + 0.1$ V
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Telecom Equipment
- Power Supply Designs
- Diesel Injection Control
- Automotive
- Motor Control

PIN CONNECTIONS

Single Channel



1





CASE 419A-02

TSOP-5 **CASE 483**



SOT-553, 5 LEAD CASE 463B

DEVICE MARKING INFORMATION

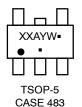


CASE 419A-02





SO-553, 5 LEAD CASE 463B



= Specific Device Code XX

= Assembly Location = Year W = Work Week M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 12 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Supply Voltage Range (V _{DD} - V _{SS})	V _S	-0.3 to 40	V
Input Common-Mode Voltage	V _{CM}	V _{SS} – 0.2 to V _{DD} + 0.2	V
Differential Input Voltage	V _{ID}	±V _S	V
Maximum Input Current	I _I	±10	mA
Maximum Output Current	I _O	±100	mA
Continuous Total Power Dissipation	P _D	200	mW
Maximum Junction Temperature	T _{J(max)}	150	°C
Storage Temperature Range	T _{STG}	-65 to 150	°C
ESD Capability, Human Body Model (Note 2)	НВМ	±2000	V
ESD Capability, Charge Device Model (Note 2)	CDM	±1000	V
Moisture Sensitivity Level	MSL	Level 1	
Lead Temperature Soldering Reflow (SMD Styles Only), Pb-Free Versions (Note 3)	T _{SLD}	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHĂRACTERISTICS and APPLICATION INFORMATION for Safe Operating Area
- This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per JEDEC standard JS-001-2017 (AEC-Q100-002) ESD Charged Device Model tested per JEDEC standard JS-002-2014 (AEC-Q100-011)
- 3. For information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D

THERMAL CHARACTERISTICS (Note 4)

Package	θ _{JA} Junction-to-Ambient Thermal Resistance	Ψ _{JT} Junction-to-Case Top Thermal Characteristic	Ψ _{JB} Junction-to-Board Thermal Characteristic	Unit
TSOP-5 / SOT23-5	254	78	150	°C/W
SC-88A / SC-70-5 / SOT-353	902	70	810	°C/W
SOT-553	238	14	134	°C/W

^{4.} Thermal parameters are based on a 2s2p board following JESD51-7 (JEDEC)

RECOMMENDED OPERATING RANGES (Note 5)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (V _{DD} – V _{SS})	Vs	2.7	36	V
Differential Input Voltage (V _{IN+} – V _{IN-})	V_{ID}	ı	±5 (Note 6)	V
Input Common-Mode Range (Note 7)	V_{CM}	V _{SS} – 0.1	V _{DD} – 2 V	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- 5. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area
- 6. The differential voltage may not exceed the supply voltage, $\pm V_S$. For supplies greater than $\dot{V}_S = 5\, \check{V}$, differential voltages up to $\pm V_S$ will consume more input current. See APPLICATION INFORMATION.
- The specified input common mode range yields the best performance. However, the input common mode range is functional up to V_{DD} + 0.1 V. See APPLICATION INFORMATION.

ELECTRICAL CHARACTERISTICS (V_S = 2.7 V to 36 V) At T_A = +25 °C, R_L = 10 kΩ connected to midsupply, V_{CM} = V_{OUT} = midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range, guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Supply Voltage (V)	Temp (°C)	Min	Тур	Max	Unit
INPUT CHARACTERISTIC	cs							
Offset Voltage	Vos	V _{CM} = mid-supply	2.7, 5, 10, 36	25	-	±0.3	±0.95	mV
				-40 to 125	-	-	±1.2	
				-40 to 150	-	-	±1.2	1
Offset Voltage Drift over	dV _{OS} /dT	V _{CM} = mid-supply	2.7, 5, 10, 36	-40 to 125	-	±0.5	±2	μV/°C
Temperature				-40 to 150	-	±0.5	±5	1
Input Bias Current	I _{IB}		2.7, 5, 10, 36	25	-	±5	±60	pА
(Note 8)				-40 to 125	-	-	±3000	
				150	-	±10000	-	
Input Offset Current	Ios		2.7	25	-	±0.5	±60	pА
(Note 8)				-40 to 125	-	_	±500	1
				-40 to 150	-	_	±2000	1
			5, 10	25	-	±0.5	±60	1
				-40 to 125	-	_	±800	1
				-40 to 150	-	_	±2500	1
			36	25	-	±0.5	±60	pА
				-40 to 125	-	_	±2000	
				-40 to 150	-	_	±2500	500
Input Capacitance	C _{IN}	IN+	2.7, 36	25	-	1	_	pF
		IN-	2.7, 36	25	-	6	-	1
Common Mode	CMRR	V _{CM} = V _{SS} - 0.1 V	2.7	25	80	98	-	dB
Rejection Ratio		to V _{DD} – 2 V		-40 to 125	75	_	_	
				-40 to 150	69	_	-	
			5	25	90	105	_	1
			(Note 8)	-40 to 125	85	_	-	
				-40 to 150	80	_	_	1
			10	25	100	117	_	1
			(Note 8)	-40 to 125	100	_	_	1
				-40 to 150	94	_	_	1
			36	25	110	122	_	1
				-40 to 125	110	_	_	1
				-40 to 150	107	_	_	1
		V _{CM} = V _{SS} + 1.8 V to V _{DD} - 2.4 V	36	25	117 (Note 8)	125	-	dB
EMI Rejection Ratio	EMIRR		2.7, 36	25	-	See Figure 29	-	dB

^{8.} Guaranteed by design and/or characterization.

ELECTRICAL CHARACTERISTICS (V_S = 2.7 V to 36 V) (continued) At T_A = +25 °C, R_L = 10 kΩ connected to midsupply, V_{CM} = V_{OUT} = midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range, guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Supply Voltage (V)	Temp (°C)	Min	Тур	Max	Unit
OUTPUT CHARACTERIST	TICS							
Open Loop Voltage Gain	A _{VOL}	V _{CM} = mid-supply	2.7	25	100	115	-	dB
				-40 to 125	90	_	_	
				-40 to 150	90	_	_	
			5	25	120	135	_	
			(Note 9)	-40 to 125	115	_	_	
				-40 to 150	115	-	-	
			10	25	130	145	-	
			(Note 9)	-40 to 125	120	-	-	
				-40 to 150	120	-	-	
			36	25	135	154	-	
				-40 to 125	130	-	-	
				-40 to 150	130	_	_	
Open Loop Output Impedance	Z _{OUT}			-	-	See Figure 28	-	Ω
High Level Output Voltage Swing from V _{DD}	V_{DD} - V_{OH}	$R_L = 10 \text{ k}\Omega$	2.7, 5, 10, 36	25	_	60	80	mV
				-40 to 125	-	-	120	
				-40 to 150	-	-	150	
		I _{OUT} = 1 mA	2.7, 5, 10, 36	25	-	40	60	
				-40 to 125	-	-	80	
				-40 to 150	-	-	100	
		I _{OUT} = 5 mA	10	25	-	165	200	
				-40 to 125	-	-	350	
				-40 to 150	-	-	400	
Low Level Output Voltage	V _{OL} -V _{SS}	$R_L = 10 \text{ k}\Omega$	2.7, 5, 10	25	-	16	30	mV
Swing from V _{SS}				-40 to 125	_	_	50	
				-40 to 150	-	-	50	
			36	25	_	55	80	
				-40 to 125	-	-	250	
				-40 to 150	-	-	120	
		I _{OUT} = 1 mA	2.7, 5, 10, 36	25	_	35	50	
				-40 to 125	-	-	80	
				-40 to 150	-	-	80	
		I _{OUT} = 5 mA	10	25	-	150	170	
				-40 to 125	-	-	300	
				-40 to 150	-	-	300	
Output Current Capability	I _{OUT}	Output to V _{DD} rail, sinking current	2.7, 5, 10, 36	25	1	28	-	mA
		Output to V _{SS} rail, sourcing current	2.7, 5, 10, 36	25	-	28	-	
Capacitive Load Drive	C_L	Phase margin = 35 °	2.7 to 36	25	-	140	-	pF

^{9.} Guaranteed by design and/or characterization.

ELECTRICAL CHARACTERISTICS (V_S = 2.7 V to 36 V) (continued) At T_A = +25 °C, R_L = 10 k Ω connected to midsupply, V_{CM} = V_{OUT} = midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range, guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Supply Voltage (V)	Temp (°C)	Min	Тур	Max	Unit
DYNAMIC PERFORMANC	E							
Gain Bandwidth Product	GWBP	C _L = 25 pF	2.7, 5, 10, 36	25	-	3	-	MHz
Gain Margin	A _m	C _L = 25 pF	2.7, 5, 10, 36	25	_	16	-	dB
Phase Margin	Φ_{m}	C _L = 25 pF	2.7, 5, 10, 36	25	-	60	-	٥
Slew Rate	SR	Unity gain, $R_L = 2 \text{ k}\Omega$	2.7, 5, 10, 36	25	-	4	-	V/μs
Settling Time to 0.1 %	t _s	V _{IN} = 1 V step	2.7	25	-	7	-	μs
		V _{IN} = 3 V step	5	25	-	7	-	1
		V _{IN} = 8 V step	10	25	-	7	-	1
		V _{IN} = 10 V step	36	25	-	6	-	1
Settling Time to 0.01 %	t _s	V _{IN} = 1 V step	2.7	25	-	20	-	μs
		V _{IN} = 3 V step	5	25	-	10	-	1
		V _{IN} = 8 V step	10	25	_	9	-	1
		V _{IN} = 10 V step	36	25	_	9	-	
NOISE PERFORMANCE								
Total Harmonic Distortion + Noise	THD+ N	$V_{IN} = 0.5 V_{pp},$ f = 1 kHz, A _V = 1	2.7	25	-	0.009	-	%
		$V_{IN} = 2.5 V_{pp},$ f = 1 kHz, A _V = 1	5	25	-	0.0004	-	
		$V_{IN} = 7.5 V_{pp},$ f = 1 kHz, A _V = 1	10	25	-	0.0002	_	1
		V _{IN} = 28.5 V _{pp} , f = 1 kHz, A _V = 1	36	25	-	0.0002	-	1
Voltage Noise		f = 1 kHz	2.7, 5, 10, 36	25	-	20	-	nV/√Hz
Density	e _n	f = 10 kHz			-	20	-	1
Current Noise Density	i _n	f = 1 kHz	2.7, 5, 10, 36	25	-	30	-	fA/√Hz
Voltage Noise, Peak to Peak	e _{pp}	f _{IN} = 0.1 Hz to 10 Hz	2.7, 5, 10, 36	25	-	700	-	nV _{pp}
POWER SUPPLY		L	Į.					
Power Supply	PSRR	Vs = 2.7 V to 36 V	2.7, 36	25	125	138	_	dB
Rejection Ratio				-40 to 125	120	_	_	1
				-40 to 150	120	_	_	1
Quiescent Current	IQ	No load	2.7, 5	25	_	0.37	0.595	mA
				-40 to 125	_	_	0.650	1
				-40 to 150	_	_	0.7	1
			10	25	_	0.375	0.595	1
				-40 to 125	_	_	0.650	1
				-40 to 150	_	_	0.75	1
			36	25	_	0.41	0.595	1
				-40 to 125	_	_	0.650	1
				-40 to 150	_	_	0.8	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

TYPICAL PERFORMANCE AT T_A = 25 °C, VCM = MID–SUPPLY, C_L = 20 PF, R_L = 10 K Ω TO MID–SUPPLY, UNLESS OTHERWISE NOTED

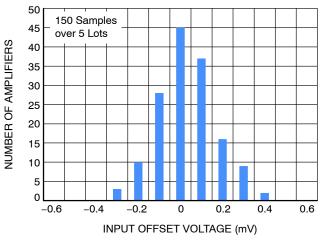


Figure 1. Input Offset Voltage Distribution

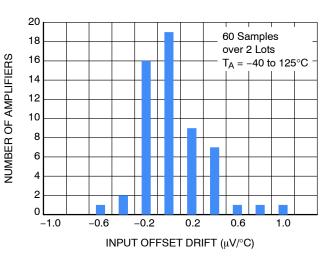


Figure 2. Input Offset Voltage Drift Distribution

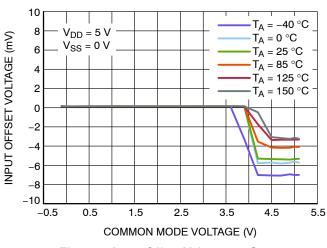


Figure 3. Input Offset Voltage vs. Common Mode Voltage

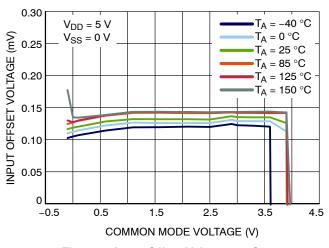


Figure 4. Input Offset Voltage vs. Common Mode Voltage, Performance Region

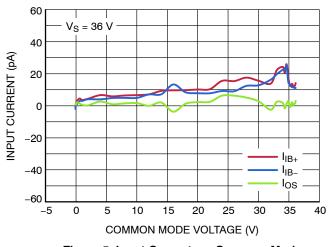


Figure 5. Input Current vs. Common Mode Voltage

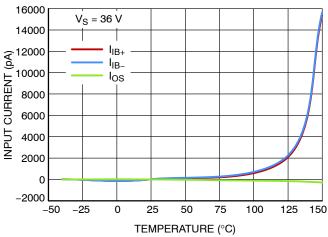
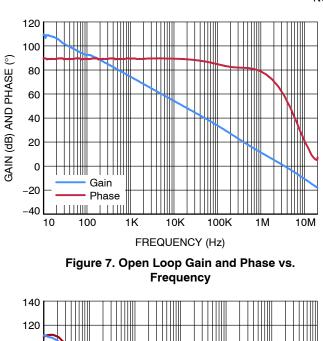


Figure 6. Input Current vs. Temperature

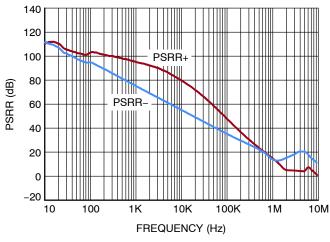
TYPICAL CHARACTERISTICS

TYPICAL PERFORMANCE AT T_A = 25 °C, VCM = MID–SUPPLY, C_L = 20 PF, R_L = 10 K Ω TO MID–SUPPLY, UNLESS OTHERWISE NOTED



120 100 80 60 40 20 0 -20 10 100 1K 10K 100K 1M 10M FREQUENCY (Hz)

Figure 8. CMRR vs. Frequency



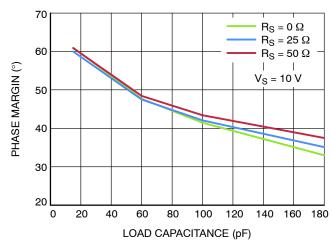
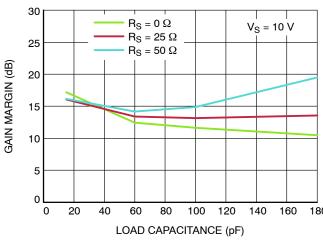


Figure 9. PSRR vs. Frequency

Figure 10. Phase Margin vs. Capacitive Load



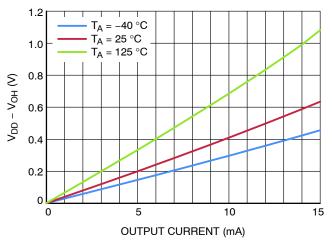


Figure 11. Gain Margin vs. Capacitive Load

Figure 12. Output Voltage Swing High vs. Output Current at $V_S = 2.7 \text{ V}$

TYPICAL CHARACTERISTICS

TYPICAL PERFORMANCE AT T_A = 25°C, VCM = MID–SUPPLY, C_L = 20 PF, R_L = 10 K Ω TO MID–SUPPLY, UNLESS OTHERWISE NOTED

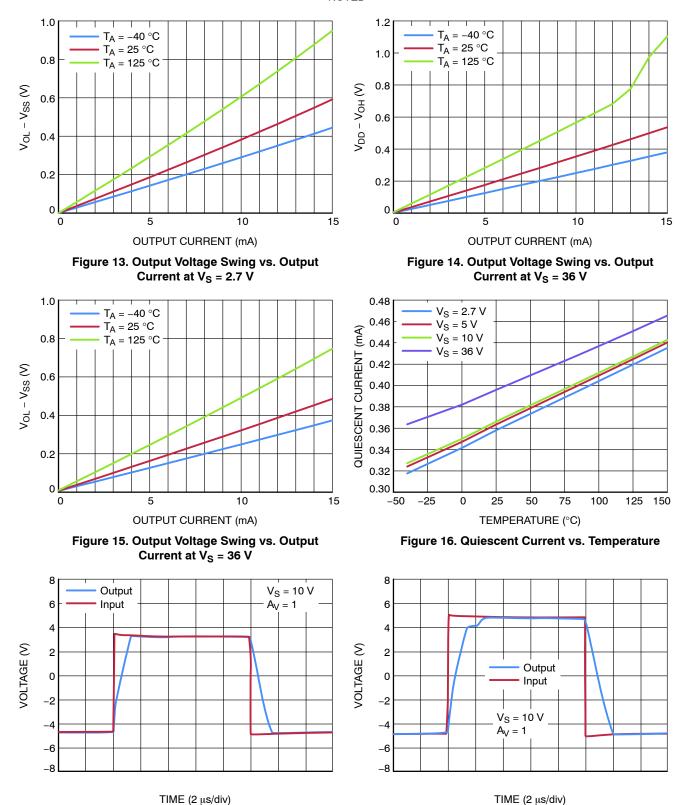


Figure 17. Large Signal Step Response

Figure 18. Large Signal Step Response

TYPICAL CHARACTERISTICS

TYPICAL PERFORMANCE AT T_A = 25 °C, VCM = MID–SUPPLY, C_L = 20 PF, R_L = 10 K Ω TO MID–SUPPLY, UNLESS OTHERWISE NOTED

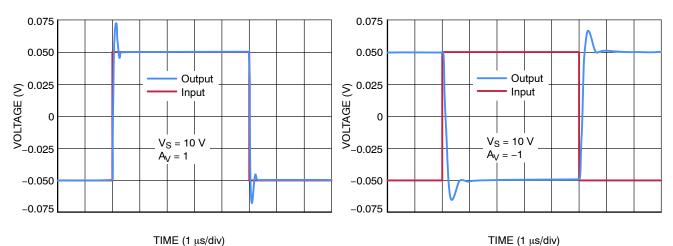


Figure 19. Small Signal Step Response

Figure 20. Small Signal Step Response

Figure 22. Output Overload Recovery

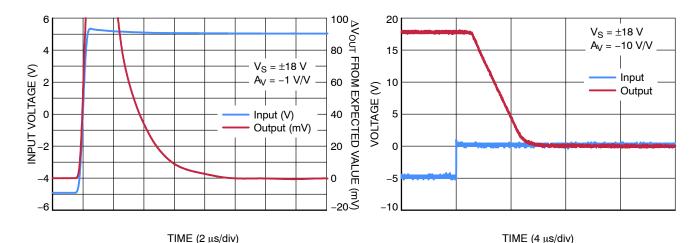


Figure 21. Settling Time

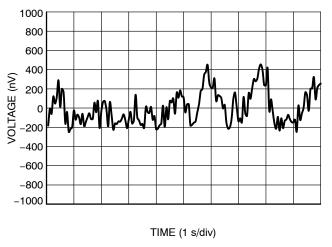
Response 8 0.001 $V_{S} = 36 \text{ V}$ Output 6 $R_L = 10 \text{ k}\Omega$ Input $V_{IN} = 28.5 V_{PP}$ 4 $A_V = 1$ VOLTAGE (V) 2 (%) u+0.0001 0 -2 -4 $V_{S} = 10 V$ -6 $A_V = 1$ 0.00001 1K 10 100 10K TIME (2 µs/div) FREQUENCY (Hz)

Figure 23. No Phase Reversal

Figure 24. THD+n vs. Frequency

TYPICAL CHARACTERISTICS

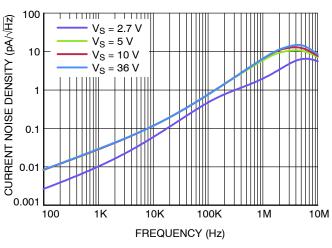
TYPICAL PERFORMANCE AT T_A = 25 °C, VCM = MID–SUPPLY, C_L = 20 PF, R_L = 10 K Ω TO MID–SUPPLY, UNLESS OTHERWISE NOTED



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Figure 25. 0.1 Hz to 10 Hz Noise

Figure 26. Voltage Noise Density vs. Frequency



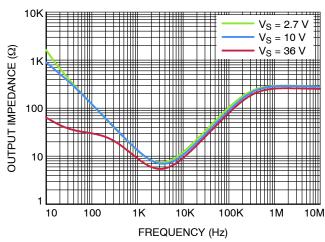
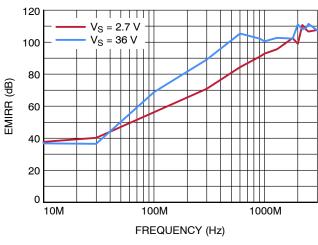


Figure 27. Current Noise Density vs. Frequency

Figure 28. Open Loop Output Impedance vs. Frequency



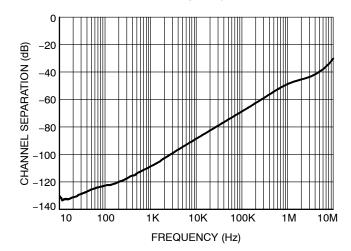


Figure 29. EMIRR vs. Frequency

Figure 30. Channel Separation vs. Frequency

APPLICATION INFORMATION

Input and ESD Structure

The NCS20231 amplifier has back-to-back Zener diodes, which allow for normal operation with the differential voltage up to ±5 V. Differential voltages beyond this are

permitted, up to $\pm V_S$, but increased input leakage current should be expected. Internal current limiting resistors in series with the input pins limit the current to ± 10 mA in scenarios where the differential voltage is as high as ± 36 V.

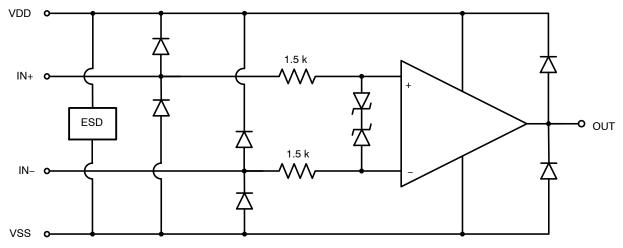


Figure 31. Representative Schematic of the Op Amp

Each input pin is diode clamped to the rails. In case of an input overvoltage, input currents must be limited to within ± 10 mA to prevent excessive current from damaging the part.

Rail-to-Rail Performance

The functional common mode input voltage spans 100 mV beyond the rails. High precision performance, as

shown throughout the ELECTRICAL CHARACTERISTICS table, is achieved in the $V_{SS}-0.1~V$ to $V_{DD}-2~V$ common mode voltage range. The input common mode extends further up to $V_{DD}+0.1~V$ to ensure functionality near the upper rail, though without precision performance in that region. The typical performance within the $V_{DD}-2~V$ to $V_{DD}+0.1~V$ range is shown in the table below.

Parameter	Symbol	Conditions	Тур	Units
Input Offset Voltage	Vos	V _{CM} = V _{DD} – 0.5 V	±9	mV
Input Offset Voltage over Temperature	dV _{OS} /dT		±24	μV/°C
Common Mode Rejection Ratio	CMRR	$V_{CM} = V_{DD} - 0.5 \text{ V to } V_{DD} + 0.1 \text{ V}$	75	dB
Open Loop Voltage Gain	A _{VOL}	V _{CM} = V _{DD} - 0.5 V	90	dB
Gain Bandwidth Product	GBWP	$V_{CM} = V_{DD} - 0.5 \text{ V}, C_L = 25 \text{ pF}$	2.5	MHz
Slew Rate	SR	Unity gain, $V_{CM} = V_{DD} - 1 V$ to $V_{DD} - 0.2 V$	1.2	V/μs
Voltage Noise Density	e _n	f = 1 kHz	1000	nV/√Hz

The NCS20231 does not exhibit output phase reversal. Phase reversal occurs in some amplifiers when the input voltage exceeds the recommended input common mode voltage range, causing the output to flip to the opposite rail.

Instead, when the input common mode voltage range is exceeded on the NCS20231, the output becomes clipped at the output, limited by the output voltage swing.

ORDERING INFORMATION

Temperature	Channels	Package	Device Part Number	Marking	Shipping [†]
Industrial and Commerc	ial				•
–40 °C to 125 °C	Single	TSOP-5	NCS20231SN2T1G	AAC	3000 / Tape & Reel
		SC-88	NCS20231SQ3T2G	AAG	3000 / Tape & Reel
		SOT-553	NCS20231XV53T2G	AC	4000 / Tape & Reel
Automotive Qualified, G	rade 1				•
-40°C to 150 °C	Single	TSOP-5	NCV20231SN2T1G	AAC	3000 / Tape & Reel
		SC-88	NCV20231SQ3T2G	AAG	3000 / Tape & Reel
		SOT-553	NCV20231XV53T2G	AC	4000 / Tape & Reel

 [†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 * In Development. Contact local sales office for more information.

REVISION HISTORY

Revision	Description of Changes	Date
5	Revision to delete dual and quad package options.	7/3/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.







SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

DATE 11 APR 2023

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS
- OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

DIM	MILLIMETERS				
ואונת	MIN.	N□M.	MAX.		
А	0.80	0.95	1.10		
A1			0.10		
A3	0.20 REF				
b	0.10	0.20	0.30		
C	0.10		0.25		
D	1.80	2.00	2,20		
Е	2.00	2.10	2.20		
E1	1.15	1.25	1.35		
е	0.65 BSC				
L	0.10	0.15	0.30		

- 419A-01 DBSDLETE, NEW STANDARD 419A-02
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS,

	L →	
<u> </u>	0.50	5

5X b

→ 0.2 M B M

RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

5. COLLECTOR

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:	98ASB42984B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-88A (SC-70-5/SOT-353)		PAGE 1 OF 1

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5. COLLECTOR 2/BASE 1





SOT-553-5 1.60x1.20x0.55, 0.50P CASE 463B ISSUE D

DATE 21 FEB 2024

MILLIMETERS

MAX.

0.60

0.27

0.18

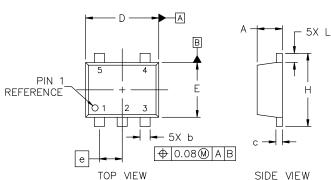
1.65

1.25

1.65

0.30

NOM.

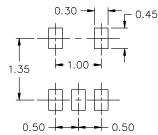


NOTES:

- . DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM

	А	0.50	0.55	
	b	0.17	0.22	
	С	0.08	0.13	
5	D	1.55	1.60	
	E	1.15	1.20	
	е	1	0.50 BSC	;
	Н	1.55	1.60	
	L	0.10	0.20	
				_



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 1 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	

DOCUMENT NUMBER:	98AON11127D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-553-5 1.60x1.20x0.55	5, 0.50P	PAGE 1 OF 1

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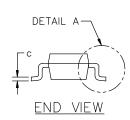
TSOP-5 3.00x1.50x0.95, 0.95P **CASE 483**

ISSUE P

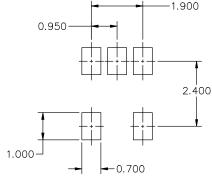
DATE 01 APR 2024

NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. 3. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.



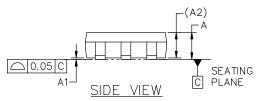
DIM	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
Α	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2	0.950 REF.		
b	0.250	0.375	0.500
С	0.100	0.180	0.260
D	2.850	3.000	3.150
E	2.500	2.750	3.000
E1	1.350	1.500	1.650
е	0.950 BSC		
L	0.200	0.400	0.600
Θ	0.	5°	10°

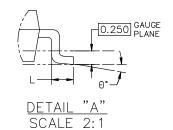


RECOMMENDED MOUNTING FOOTPRINT*

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NOTE 5 В Ė1 PIN 1 **IDENTIFIER** ΙAŀ TOP VIEW





GENERIC MARKING DIAGRAM*





= Date Code

= Pb-Free Package

Analog Discrete/Logic XXX = Specific Device Code

XXX = Specific Device Code = Assembly Location

= Year W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

М

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DOCUMENT NUMB	En:

98ARB18753C

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DESCRIPTION:

TSOP-5 3.00x1.50x0.95, 0.95P

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